

## AMENDMENTS TO THE CLAIMS

**1. (Currently Amended)** A method for manufacturing a ferroelectric device, said method comprising:

- providing a substrate;
- forming a multi layer body by depositing successively a contact film, a lower electrode, a ferroelectric film and an upper electrode on said substrate; and
- processing said multi layer body,

wherein said processing comprises:

- forming a hard mask on said upper electrode as an etching stopper;
- etching said upper electrode and said ferroelectric film through said hard mask;
- heat treating said ferroelectric film in an oxidizing atmosphere under a condition of covering said contact film with said lower electrode;
- forming a first cover film so as to cover side surfaces of said upper electrode and said ferroelectric film and the top surface of said hard mask; ~~and~~
- etching, in a self-alignment manner with said ~~hard mask~~ first cover film, said lower electrode and said contact film to expose said substrate; and
- forming a second cover film so as to cover said multi layer body after said etching of said lower electrode and said contact film.

**2. (Previously Presented)** The method for manufacturing a ferroelectric device according to claim 1,

wherein said substrate comprises a semiconductor substrate having a transistor and an insulating film disposed on said semiconductor substrate, and

wherein a contact plug is formed so as to pass through said insulating film so as to electrically connect said transistor to said contact film.

**3. (Previously Presented)** The method for manufacturing a ferroelectric device according to claim 1, wherein at least a part of said lower electrode is etched in said first etching of said upper electrode and said ferroelectric film.

**4. (Previously Presented)** The method for manufacturing a ferroelectric device according to claim 1,

wherein said etching of said lower electrode and said contact film includes etching said first cover film together with said multi layer body.

**5-6. (Cancelled)**

**7. (Previously Presented)** The method for manufacturing a ferroelectric device according to claim 4, further comprising:

forming a resist pattern on said first cover film before said etching of said lower electrode and said contact film.

**8. (Canceled)**

**9. (Previously Presented)** The method for manufacturing a ferroelectric device according to claim 8, further comprising:

heat treating said ferroelectric film after said forming of the second cover film.

**10. (Original)** The method for manufacturing a ferroelectric device according to claim 1, wherein said contact film includes a binding film.

**11. (Original)** The method for manufacturing a ferroelectric device according to claim 10, wherein said contact film further includes an oxidation barrier film.

**12. (Previously Presented)** The method for manufacturing a ferroelectric device according to claim 1, wherein said heat treating is performed to recover a crystalline structure in the ferroelectric film.

**13. (Previously Presented)** The method for manufacturing a ferroelectric device according to claim 9, wherein said heat treating of said ferroelectric film after said forming of the second cover film is performed to recover a crystalline structure of the ferroelectric film.

**14-20. (Cancelled)**